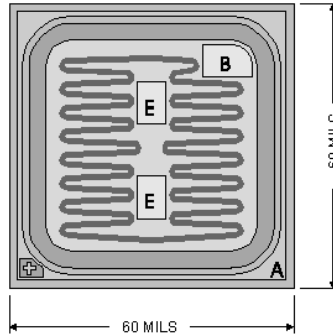


**Chip Type 2C3506**  
**Geometry 1506**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N3506, 2N3507**



[Request Quotation](#)

Chip type **2C3506** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

[2N3506](#), [2N3506L](#), [2N3507](#), [2N3507L](#)

**Product Summary:**

**APPLICATIONS:** Designed for high current, high speed saturated switching and core driver applications.

**Features:**

High current and high speed capability

Mechanical Specifications		
Metallization	Top	Al - 22 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	9.0 mils x 6.0 mils
	Base	7.0 mils x 11.0 mils
Die Thickness	8 mils nominal	
Chip Area	60 mils x 60 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	40	---	V dc
$BV_{CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	60	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5.0	---	V dc
$h_{FE}$	$I_C = 500 \text{ mA dc}, V_{CE} = 1.0 \text{ V}$	50	---	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*